EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3453	(438/149).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/20 13:10
S54	3	"20050174845"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S55	2	WO near2 "9607300"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S56	1	1996-160638.NRAN.	DERWENT	ADJ	ON	2010/06/04 18:10
S57	18	"5195010"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S58	5633	heat$3 with silicon with (voltage or current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S59	317	(chang$3 or alter$3 or convert$3) with silicon with (current or voltage) with heat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S60	2	(chang$3 or alter$3 or convert$3) with silicon with (current or voltage) with heat$3 with (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S61	15	(chang$3 or alter$3 or convert$3) with ((poly silicon) or (polycrystalline silicon) or (poly$1Si)) with (current or voltage)	US-PGPUB; USPAT; USOCR;	ADJ	ON	2010/06/04 18:10

		with heat$3	FPRS; EPO; JPO; DERWENT; IBM_TDB			
S62	10	(chang$3 or alter$3 or convert$3) with (SiGe or (silicon germanium)) with (current or voltage) with heat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S63	662	(MURAKAMI near2 SHIGERU).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S64	29	(YAMAGATA near2 YASUJI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S65	4485	(257/16,49,52,59).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S66	724	(257/64,68).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S67	1281	(257/770-772).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S68	390	(438/153).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S69	1654	(438/166).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S70	3009	(438/238-239).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S71	1476	(438/478).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S72	3	"20020126108"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S73	13807	((write near2 once) memory) or (WOM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

S74	12417	(semiconductor (film or material)) same ((amorphous silicon) or (a$1silicon) or (a$1Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S75	63	S73 and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S76	10427	((write near2 once) memory) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S77	24817	(semiconductor (film or material)) same ((amorphous silicon) or (a$1silicon) or (a$1Si) or (SiGe) or (Silicon Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S78	238	S76 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S79	291	((gate or dielctric or insulat$3) and (semiconductor)) and (((write near2 once) memory) or (one time programmable) or (OTP)).ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S80	8	((thin film transistor) or (thinfilm transistor) or TFT) and S79	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S81	1	jp "56044198"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S82	185	"20030198077" "20050098811" "20050194645" "20060054894" "20060175648" "5850090" "5994730" "6384439" "6465828" "6555420" "6576948" "6583490" "6690031"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO;	OR	ON	2010/06/04 18:11

		"6958740" "7113420" "7368343"	DERWENT; IBM_TDB			
S83	53854	voltage same increas$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S84	51204	(((write near2 once) memory) or (one time programmable) or (OTP)) and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S85	2657	(((thin film transistor) or (thinfilm transistor) or TFT) and S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S86	136	memory.ti. and S85	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S87	1278	((apply$3 or programm$4 or operat$3) near3 voltage) same (alter$3 or chang$3 or convert$3) same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S88	229	(((thin film transistor) or (thinfilm transistor) or TFT) and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S89	10	(((write near2 once) memory) or (one time programmable) or (OTP)) and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S90	2702	voltage same increas$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S91	20	(((write near2 once) memory) or (one time programmable) or (OTP)) and S90	US-PGPUB; USPAT; USOCR;	ADJ	ON	2010/06/04 18:11

			FPRS; EPO; JPO; DERWENT; IBM_TDB			
S92	1	10/573527	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/03/31 12:54
S93	44	"5854494"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:27
S94	93	"5426605"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:42
S95	1	JP "09504657"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:46
S96	1	JP "06209092"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:51
S97	2	JP "11040758"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:51
S98	0	EP "0724777"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:54
S99	0	EP "0588402"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:55
S100	0	EP0588402	US-PGPUB;	ADJ	ON	2011/04/04

						10:55
			USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB			
S101	0	EP "0588402"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/04/04 10:55
S102	959	(KATO near2 KIYOSHI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:32
S103	429	(YAMAGUCHI near2 TETSUJI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:33
S104	33	(ASANO near2 ETSUKO).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:33
S105	115	(IZUMI near2 KONAMI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:33
S106	721	(G11C17/16).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 11:46
S107	2432	(H01L21/8246).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 11:46
S108	5732	(H01L27/115).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 11:46
S109	6658	(H01L27/12).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 11:47
S110	266	((chang$3 or alter$3 or convert$3) same (current or voltage)) and S102	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:48

S111	44	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3)) and S102	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 11:49
S112	12	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S102	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:11
S113	8	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S103	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:11
S114	3	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S104	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:11
S115	7	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S105	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:11
S116	34	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S106	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:11
S118	217	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S108	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:12
S119	335	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S109	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 12:12
S120	7	((chang$3 or alter$3 or convert$3) near7 (current or voltage) near7 semi$1conductor near7 (insulat$3 or dielectrc or non$1conduct$3)) and S109	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO;	ADJ	ON	2011/09/19 12:46

			DERWENT; IBM_TDB			
S121	2432	(H01L21/8246).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 15:28
S122	65	((chang$3 or alter$3 or convert$3) same (current or voltage) same (insulat$3 or dielectrc or non$1conduct$3) same semi$1conductor) and S121	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 15:28
S123	0	((chang$3 or alter$3 or convert$3) near7 (current or voltage) near7 semi$1conductor near7 (insulat$3 or dielectrc or non$1conduct$3)) and S121	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2011/09/19 15:29
S125	30	("20030071296" | "20030198085" | "20030206467" | "20040031853" | "20040047218" | "20040125671" | "20040156234" | "20040208055" | "20040223363" | "20040223370" | "20050169039" | "20050184754" | "20070091663" | "6650143" | "6791891").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2011/09/19 17:30
S126	721	(G11C17/16).IPCR.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:02
S127	2509	(257/64-66).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S128	5802	(257/347,350).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S129	1548	(257/208-209).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S130	716	(438/157).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S131	1022	(257/E21.411).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S132	264	(257/E21.662).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:22
S133	610	(257/E21.68).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:23
S134	8452	(257/E27.103).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:23
S135	4802	(257/E27.112).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:23
S136	1132	(257/E27.102).CCLS.	US-PGPUB;	OR	OFF	2011/09/19

			USPAT; USOCR			18:23
S137	5766	(257/E27.111).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:23
S138	655	(438/482).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2011/09/19 18:26

9/20/2011 1:35:50 PM
H:\ EAST\ Workspaces\ 10573527_final.wsp